

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	13	(transistor fet mos mosfet (field adj effect)) same (gate source drain) same (liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact) same (trace wir\$6 line interconnect\$6)	US-PGPUB; USPAT	OR	ON	2005/05/16 07:43
L2	13	(transistor fet mos mosfet (field adj effect) gate source drain) and (liner etchstop (etch adj stop) nitride) and ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (via opening hole contact trace wir\$6 line interconnect\$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 07:46
L3	224	(transistor fet mos mosfet (field adj effect) gate source drain) same (liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact trace wir\$6 line interconnect\$6)	US-PGPUB; USPAT	OR	ON	2005/05/16 07:56
L4	111	(liner etchstop (etch adj stop) nitride) and ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (via opening hole contact trace wir\$6 line interconnect\$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 08:13
L5	345	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and ((liner etchstop (etch adj stop) nitride) same ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) same (via opening hole contact trace wir\$6 line interconnect\$6))	US-PGPUB; USPAT	OR	ON	2005/05/16 08:20

L6	53	((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and ((438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and (hmds hexamethyldisilazane (silane adj coupler) (metal adj coupler)))	US-PGPUB; USPAT	OR	ON	2005/05/16 08:33
L7	19	((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric)))) and (borderless near contact)	US-PGPUB; USPAT	OR	ON	2005/05/16 08:47
L8	11	(borderless near contact) same ("low-k" "low k" (low adj (permittivity dielectric)))	US-PGPUB; USPAT	OR	ON	2005/05/16 08:49
L9	56	(borderless near contact) and (interlayer ild imd organic porous)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 08:49
L10	81	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and (borderless near contact)	US-PGPUB; USPAT	OR	ON	2005/05/16 08:51
L11	87	(porous near (silica (silicon adj (oxide dioxide)))) and ("low-k" "low k" (low adj (permittivity dielectric)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/16 08:55
L12	125	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and ((porous near (silica (silicon adj (oxide dioxide)))) same ("low-k" "low k" (low adj (permittivity dielectric))))	US-PGPUB; USPAT	OR	ON	2005/05/16 09:03

L13	1361	(438/623.ccls. 438/624.ccls. 438/637.ccls. 438/638.ccls. 438/675.ccls. 438/763.ccls. 438/780.ccls. 257/635.ccls. 257/637.ccls. 257/642.ccls. 257/774.ccls. 257/775.ccls. 257/e23.145.ccls.) and ((interlayer ild imd organic porous) with ("low-k" "low k" (low adj (permittivity dielectric))))	US-PGPUB; USPAT	OR	ON	2005/05/16 09:12
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